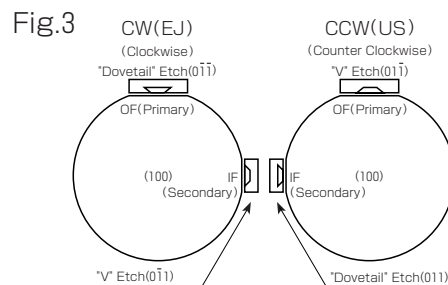
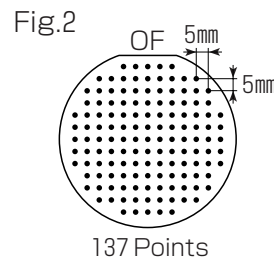
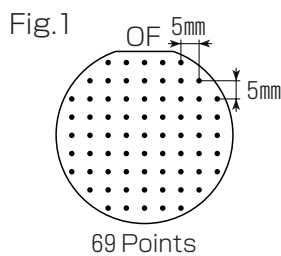


# InP Single Crystal Wafers(p-Type)

## Standard Specifications

|   |                                  |                    |
|---|----------------------------------|--------------------|
| Growth Method·Dopant                      | VCZ(*1)·Zn                       |                    |
| Carrier Concentration (cm <sup>-3</sup> ) | 2~6×10 <sup>18</sup>             |                    |
| Resistivity (Ω·cm)                        | 2~7×10 <sup>-2</sup>             |                    |
| Mobility (cm <sup>2</sup> /V·sec)         | 35~80                            |                    |
| EPD Average (cm <sup>-2</sup> )           | ≤5×10 <sup>2</sup>               | ≤5×10 <sup>3</sup> |
| EPD Guaranteed Area (*2)                  | 100%                             |                    |
| Measuring Points of EPD                   | Fig.1                            | Fig.2              |
| Diameter (mm)                             | 50.0±0.3                         | 76.0±0.3           |
| OF (mm) (Fig.3) (*3)                      | 16.0±1.0                         | 22.0±1.0           |
| IF (mm) (Fig.3)                           | 7.0±1.0                          | 12.0±1.0           |
| Edge Rounding (mmR)                       | 0.25 (Conform to SEMI Standards) |                    |
| Thickness (μm)                            | 350±15                           | 600±15             |
| Orientation                               | (100) ±0.3°                      |                    |
| Surface Finish                            | P/LE                             | P/LE               |
|   | P/P                              | P/P                |
| Surface Clean (*4)                        | EW                               |                    |
| Flatness·LPD (*5)                         | Refer to Page 8                  |                    |
| Package                                   | Individual Container             |                    |



## Notes

- (\*1) VCZ : Vapor Pressure Controlled Czochralski
- (\*2) EPD Guaranteed Area : Percentage of points within the spec.
- (\*3) High Precision OF (±0.02°) is available for 2"φ.
- (\*4) EW : Etched Wafer
- (\*5) LPD : Light Point Defects

## Attached Data

- Standard : Resistivity · Mobility · Diameter · OF · IF · Thickness (min.~max.)  
EPD Map
- Option : Accuracy of Orientation · Flatness · Light Point Defects